

ABSTRACT OF THE DISCLOSURE

The invention provides a substrate device having thin film transistors (TFTs), each including a semiconductor layer and capacitors formed above the TFTs, that are provided on a substrate. Each of the capacitors can include a first electrode electrically connected to a part of the semiconductor layer, a second electrode arranged to face the first electrode, and a dielectric film including a nitride film arranged between the first electrode and the second electrode on the substrate. Further, the nitride film has an aperture facing the semiconductor layer as seen in plan view. Accordingly, it is possible to effectively hydrogenate the semiconductor layer using the aperture.